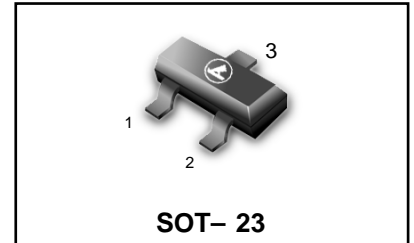


General Purpose Transistors

NPN Silicon

- We declare that the material of product compliance with RoHS requirements.

LMBT2222LT1G
LMBT2222ALT1G

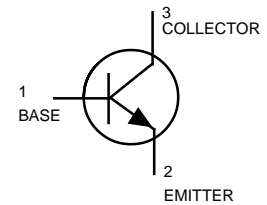


MAXIMUM RATINGS

Rating	Symbol	2222	2222A	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current — Continuous	I_C	600	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



ORDERING INFORMATION

Device	Marking	Shipping
LMBT2222LT1G	M1B	3000/Tape & Reel
LMBT2222LT3G	M1B	10000/Tape & Reel
LMBT2222ALT1G	1P	3000/Tape & Reel
LMBT2222ALT3G	1P	10000/Tape & Reel

DEVICE MARKING

LMBT2222LT1G = M1B; LMBT2222ALT1G = 1P

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 10\text{ mAdc}, I_E = 0$)	LMBT2222 LMBT2222A	$V_{(BR)CEO}$	30 40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{Adc}, I_E = 0$)	LMBT2222 LMBT2222A	$V_{(BR)CBO}$	60 75	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}, I_C = 0$)	LMBT2222 LMBT2222A	$V_{(BR)EBO}$	5.0 6.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}, I_{EB(off)} = 3.0\text{ Vdc}$)	LMBT2222A	I_{CEX}	—	10	nAdc
Collector Cutoff Current ($V_{CB} = 50\text{ Vdc}, I_E = 0$)	LMBT2222	I_{CBO}	—	0.01	μAdc
($V_{CB} = 60\text{ Vdc}, I_E = 0$)	LMBT2222A		—	0.01	
($V_{CB} = 50\text{ Vdc}, I_E = 0, T_A = 125^\circ\text{C}$)	LMBT2222		—	10	
($V_{CB} = 60\text{ Vdc}, I_E = 0, T_A = 125^\circ\text{C}$)	LMBT2222A		—	10	
Emitter Cutoff Current ($V_{EB} = 3.0\text{ Vdc}, I_C = 0$)	LMBT2222A	I_{EBO}	—	100	nAdc
Base Cutoff Current ($V_{CE} = 60\text{ Vdc}, V_{EB(off)} = 3.0\text{ Vdc}$)	LMBT2222A	I_{BL}	—	20	nAdc

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

LMBT2222LT1G LMBT2222ALT1G
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
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DC CHARACTERISTICS

DC Current Gain	h_{FE}			—
(I _C = 0.1 mAdc, V _{CE} = 10 Vdc)		35	—	
(I _C = 1.0 mAdc, V _{CE} = 10 Vdc)		50	—	
(I _C = 10 mAdc, V _{CE} = 10 Vdc)		75	—	
(I _C = 10 mAdc, V _{CE} = 10 Vdc, T _A = -55°C)	LMBT2222A only	35	—	
(I _C = 150 mAdc, V _{CE} = 10 Vdc) (3)		100	300	
(I _C = 150 mAdc, V _{CE} = 1.0 Vdc) (3)		50	—	
(I _C = 500 mAdc, V _{CE} = 10 Vdc)(3)	LMBT2222	30	—	
	LMBT2222A	40	—	
Collector–Emitter Saturation Voltage(3)	V _{CE(sat)}			Vdc
(I _C = 150 mAdc, I _B = 15 mAdc)	LMBT2222	—	0.4	
	LMBT2222A	—	0.3	
(I _C = 500mAdc, I _B = 50 mAdc)	LMBT2222	—	1.6	
	LMBT2222A	—	1.0	
Base–Emitter Saturation Voltage	V _{BE(sat)}			Vdc
(I _C = 150 mAdc, I _B = 15 mAdc)	LMBT2222	—	1.3	
	LMBT2222A	0.6	1.2	
(I _C = 500 mAdc, I _B = 50 mAdc)	LMBT2222	—	2.6	
	LMBT2222A	—	2.0	

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product(4)	LMBT2222	f _T	250	—	MHz
(I _C = 20mAdc, V _{CE} = 20Vdc, f = 100MHz)	LMBT2222A		300	—	
Output Capacitance(V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	—	8.0	pF
Input Capacitance	LMBT2222	C _{ibo}	—	30	pF
(V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	LMBT2222A		—	25	
Input Impedance(V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	LMBT2222A	h _{ie}	2.0	8.0	kΩ
(V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)	LMBT2222A		0.25	1.25	
Voltage Feedback Ratio(V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	LMBT2222A	h _{re}	—	8.0	X 10 ⁻⁴
(V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)	LMBT2222A		—	4.0	
Small–Signal Current Gain(V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	LMBT2222A	h _{fe}	50	300	—
(V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)	LMBT2222A		75	375	
Output Admittance(V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	LMBT2222A	h _{oe}	5.0	35	μmhos
(V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)	LMBT2222A		25	200	
Current Base Time Constant		r _b , C _C	—	150	ps
(V _{CB} = 20 Vdc, I _E = 20 mAdc, f = 31.8 MHz)	LMBT2222A				
Noise Figure(V _{CE} = 10 Vdc, I _C = 100 μAdc, R _S = 1.0 kΩ, f = 1.0 kHz)	LMBT2222A	NF	—	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 30 Vdc, V _{EB(off)} = -0.5 Vdc)	t _d	—	10	ns
Rise Time	I _C = 150 mAdc, I _{B1} = 15 mAdc)	t _r	—	25	
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc)	t _s	—	225	ns
Fall Time	I _{B1} = I _{B2} = 15 mAdc)	t _f	—	60	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4. f_T is defined as the frequency at which |h_{ie}| extrapolates to unity.

LMBT2222LT1G LMBT2222ALT1G

SWITCHING TIME EQUIVALENT TEST CIRCUITS

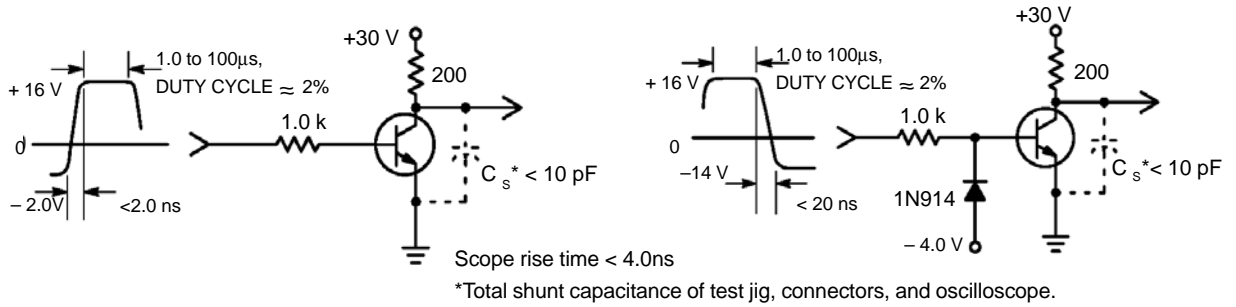
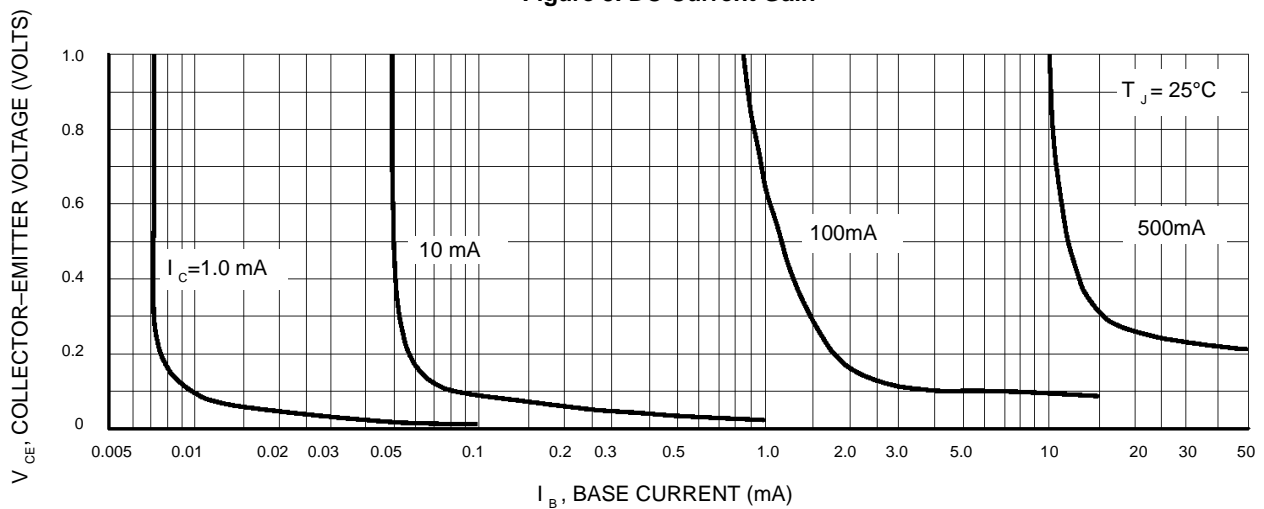
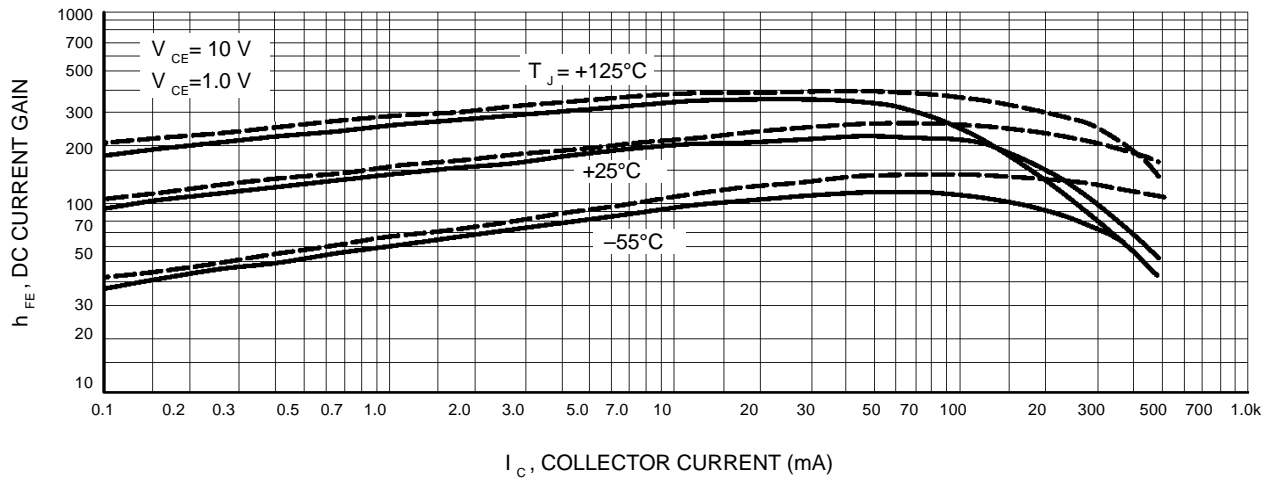


Figure 1. Turn-On Time

Figure 2. Turn-Off Time



LMBT2222LT1G LMBT2222ALT1G

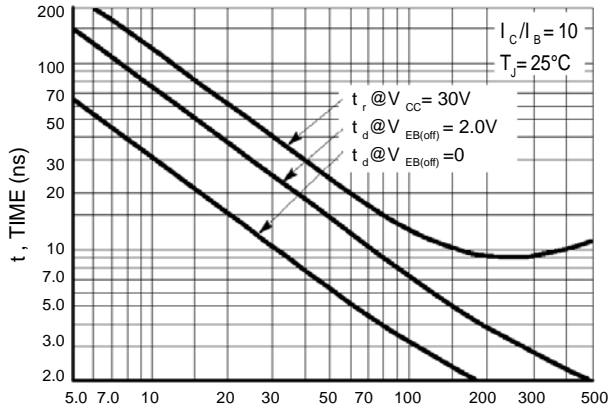


Figure 5. Turn-On Time

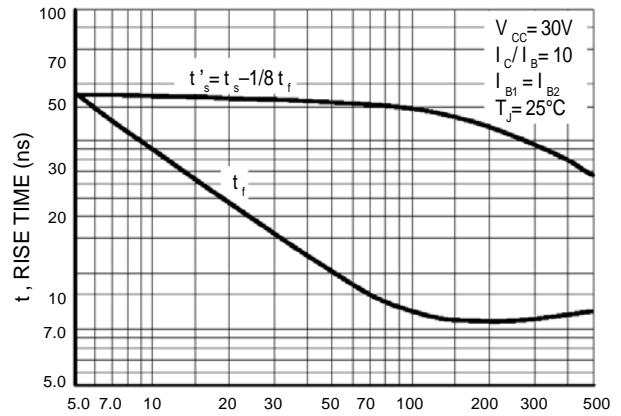


Figure 6. Turn - Off Time

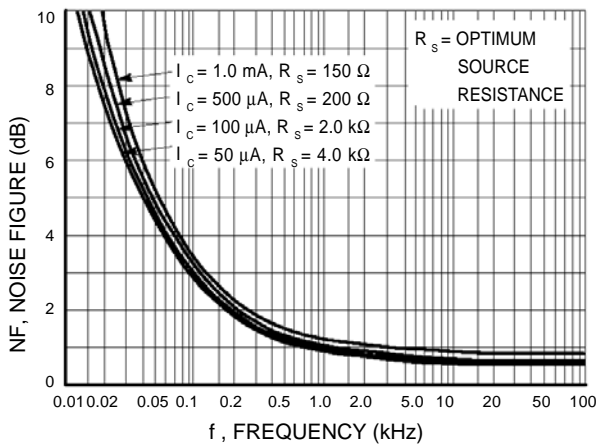


Figure 7. Frequency Effects

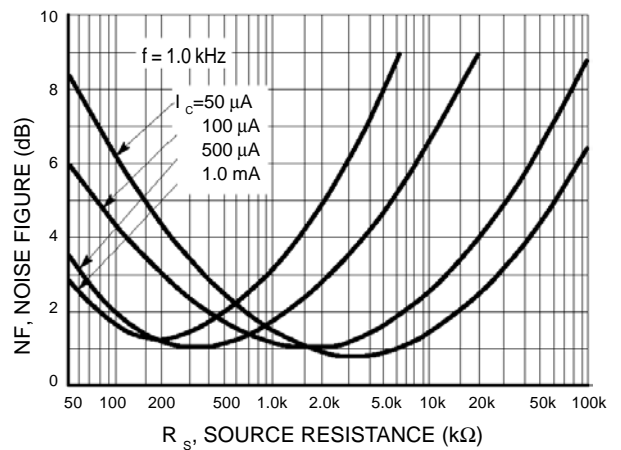


Figure 8. Source Resistance Effects

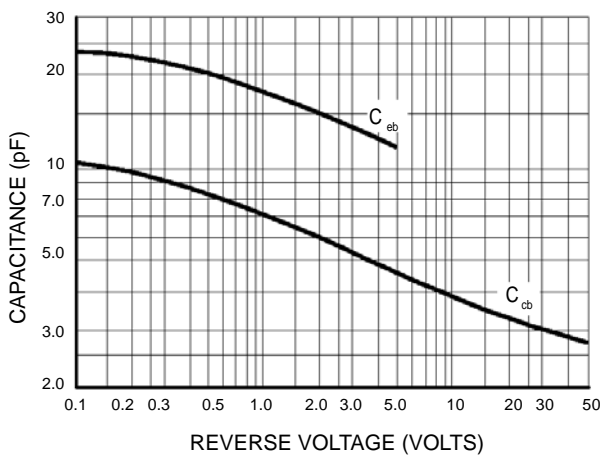


Figure 9. Capacitance

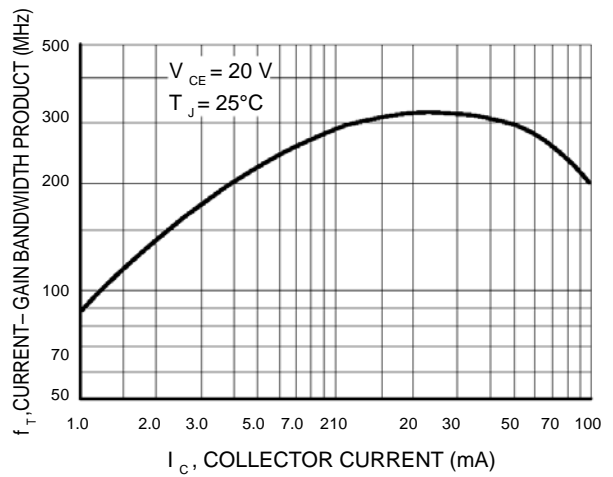


Figure 10. Current-Gain Bandwidth Product

LMBT2222LT1G LMBT2222ALT1G

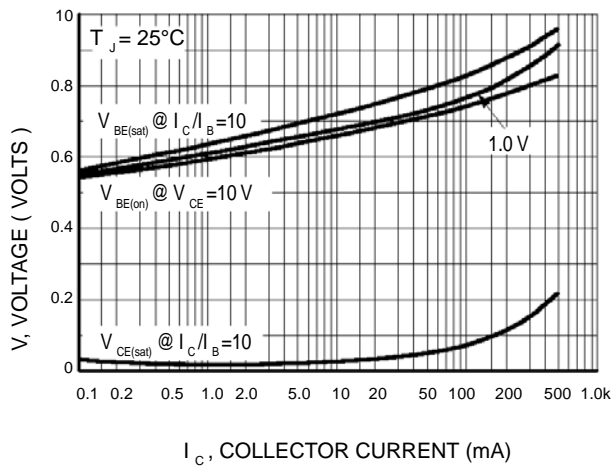


Figure 11. "On" Voltages

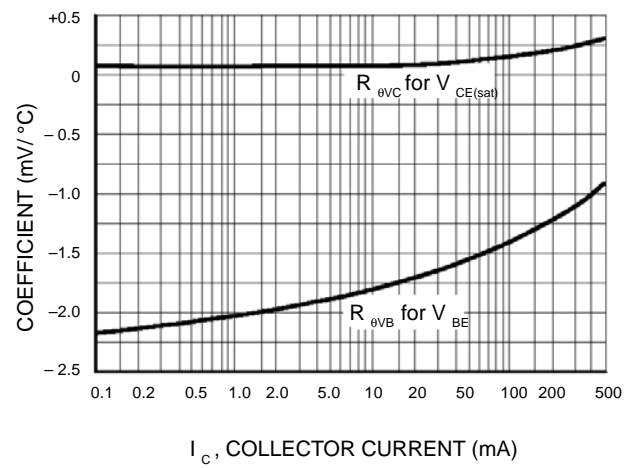
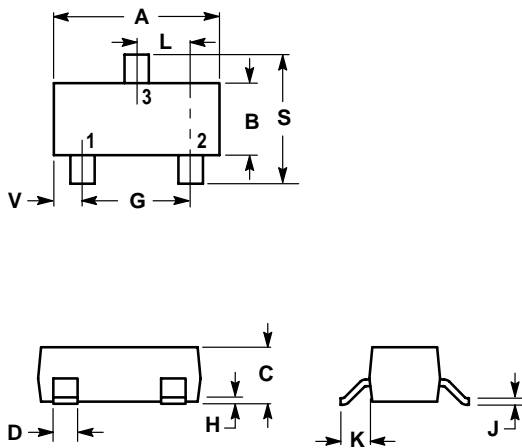


Figure 12. Temperature Coefficients

LMBT2222LT1G LMBT2222ALT1G
SOT-23
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

